

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

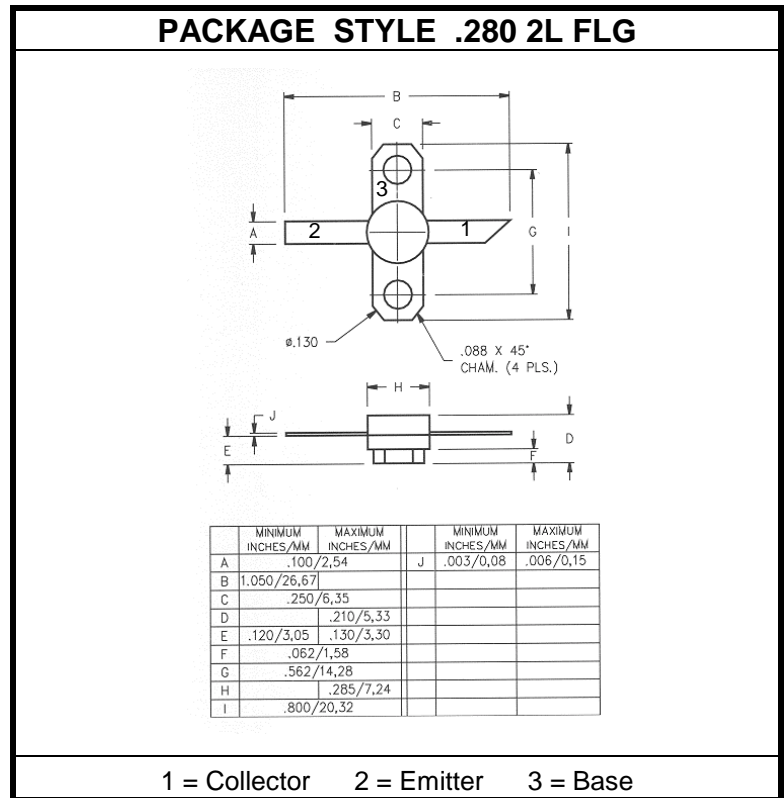
The **ASI MSC1015M** is Designed for Class C, DME/TACAN Applications up to 1150 MHz.

FEATURES:

- Class C Operation
- $P_G = 10$ dB at 15 W/1150 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	1.25 A PEAK
V_{CB}	50 V
P_{DISS}	88 W PEAK
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.0 °C/W


CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 10$ mA	65			V
BV_{CER}	$I_C = 10$ mA $R_{BE} = 10$ Ω	65			V
BV_{EBO}	$I_E = 1.0$ mA	3.5			V
I_{CES}	$V_{CB} = 50$ V			2.5	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 500$ mA	15		120	---
P_G	$V_{CC} = 50$ V $P_{OUT} = 15$ W $f = 1025 - 1150$ MHz	10			dB
η_c	$P_{IN} = 1.5$ W	35			%

Pulse width = 10 μ Sec, Duty Cycle = 1 %